

# **High Voltage Transistor** PNP Silicon

# **BF493S**

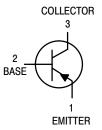
## **MAXIMUM RATINGS**

Rating	Symbol	Value	ue Unit	
Collector–Emitter Voltage	VCEO	-350	Vdc	
Collector-Base Voltage	VCBO	-350	Vdc	
Emitter-Base Voltage	V <sub>EBO</sub>	-6.0	Vdc	
Collector Current — Continuous	IC	-500	mAdc	
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0	Watts mW/°C	
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	



# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W



# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS	OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (1) (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	-350	_	Vdc	
Collector–Base Breakdown Voltage (I <sub>C</sub> = –100 μAdc, I <sub>E</sub> = 0)	V(BR)CBO	-350	_	Vdc	
Emitter–Base Breakdown Voltage (IE = $-100 \mu Adc$ , IC = 0)	V(BR)EBO	-6.0	_	Vdc	
Collector Cutoff Current (V <sub>CE</sub> = -250 Vdc)	ICES	_	-10	nAdc	
Emitter Cutoff Current (VEB = -6.0 Vdc, IC = 0)	IEBO	_	0.1	μAdc	
Collector Cutoff Current $(V_{CB} = -250 \text{ Vdc}, I_E = 0, T_A = 25^{\circ}\text{C})$ $(V_{CB} = -250 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	ICBO	— —	-0.005 -1.0	μAdc	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu s$ ; Duty Cycle  $\leq 2.0\%$ .

# **BF493S**

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain (I <sub>C</sub> = $-1.0$ mAdc, V <sub>CE</sub> = $-10$ Vdc) (I <sub>C</sub> = $-10$ mAdc, V <sub>CE</sub> = $-10$ Vdc)	hFE	25 40	_	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = -20 mAdc, I <sub>B</sub> = -2.0 mAdc)	VCE(sat)	_	-2.0	Vdc
Base–Emitter On Voltage $(I_C = -20 \text{ mA}, I_B = -2.0 \text{ mA})$	VBE(sat)	_	-2.0	Vdc
DYNAMIC CHARACTERISTICS			•	
Current–Gain — Bandwidth Product ( $I_C = -10 \text{ mAdc}$ , $V_{CE} = -20 \text{ Vdc}$ , $f = 20 \text{ MHz}$ )	fT	50	_	MHz
Common–Emitter Feedback Capacitance (V <sub>CB</sub> = -100 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>re</sub>	_	1.6	pF

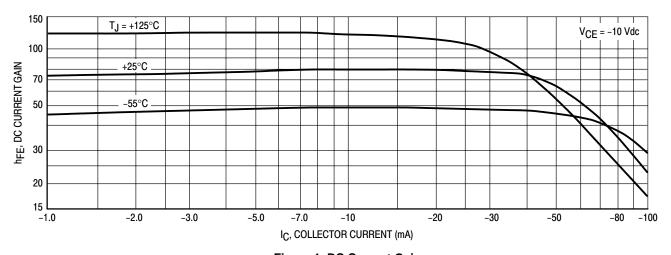


Figure 1. DC Current Gain

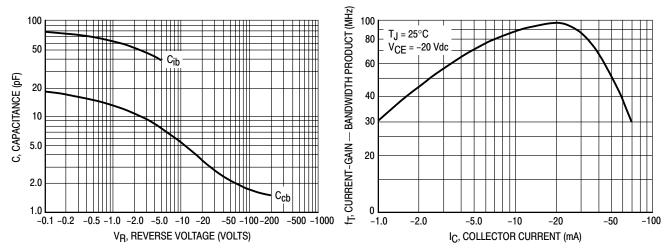
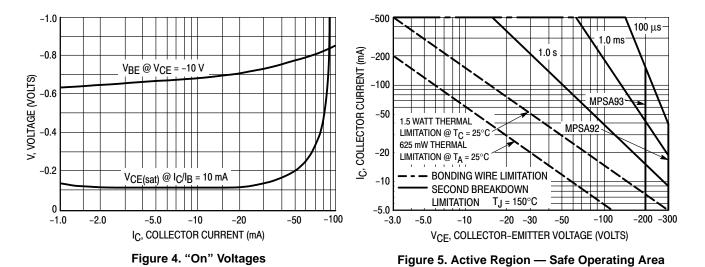


Figure 3. Current-Gain — Bandwidth Product

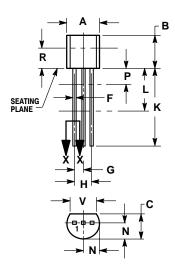
Figure 2. Capacitances

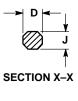


#### **BF493S**

#### PACKAGE DIMENSIONS

CASE 029-04 (TO-226AA) ISSUE AD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   Y14 5M 1982
- 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L.
   DIMENSION D AND J APPLY BETWEEN L AND K
   MINIMUM. LEAD DIMENSION IS UNCONTROLLED
   IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
C	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
v	0 135		3 //3		

STYLE 1:

PIN 1. EMITTER 2. BASE 3. COLLECTOR

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

#### **PUBLICATION ORDERING INFORMATION**

## Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

**Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031

Phone: 81–3–5740–2700 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.